

**Silicon PNP Power Transistors****2SA980/981/982****DESCRIPTION**

- With TO-3 package
- Complement to type 2SC2260/2261/2262

APPLICATIONS

- For power switching and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Fig.1 simplified outline (TO-3) and symbol****Absolute maximum ratings(Ta=℃)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA980	Open emitter	-100	V
		2SA981		-120	
		2SA982		-140	
V_{CEO}	Collector-emitter voltage	2SA980	Open base	-100	V
		2SA981		-120	
		2SA982		-140	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-8	A
I_B	Base current			-3	A
P_C	Collector power dissipation		$T_C=25^{\circ}\text{C}$	80	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-65~150	℃

**Silicon PNP Power Transistors****2SA980/981/982****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA980	I _C =-50mA ; I _B =0	-100			V
		2SA981		-120			
		2SA982		-140			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-3A; I _B =-0.3A			-1.5	V
I _{CBO}	Collector cut-off current	2SA980	V _{CB} =-100V; I _E =0			-0.1	mA
		2SA981	V _{CB} =-120V; I _E =0				
		2SA982	V _{CB} =-140V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain		I _C =-3A ; V _{CE} =-4V	30			
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-12V		20		MHz

Switching times

t _r	Rise time	I _C =-3A; R _L =4 Ω I _{B1} =-0.2A; I _{B2} =0.1A V _{CC} =-12V		0.85		μ s
t _s	Storage time			2.0		μ s
t _f	Fall time			0.3		μ s



PACKAGE OUTLINE

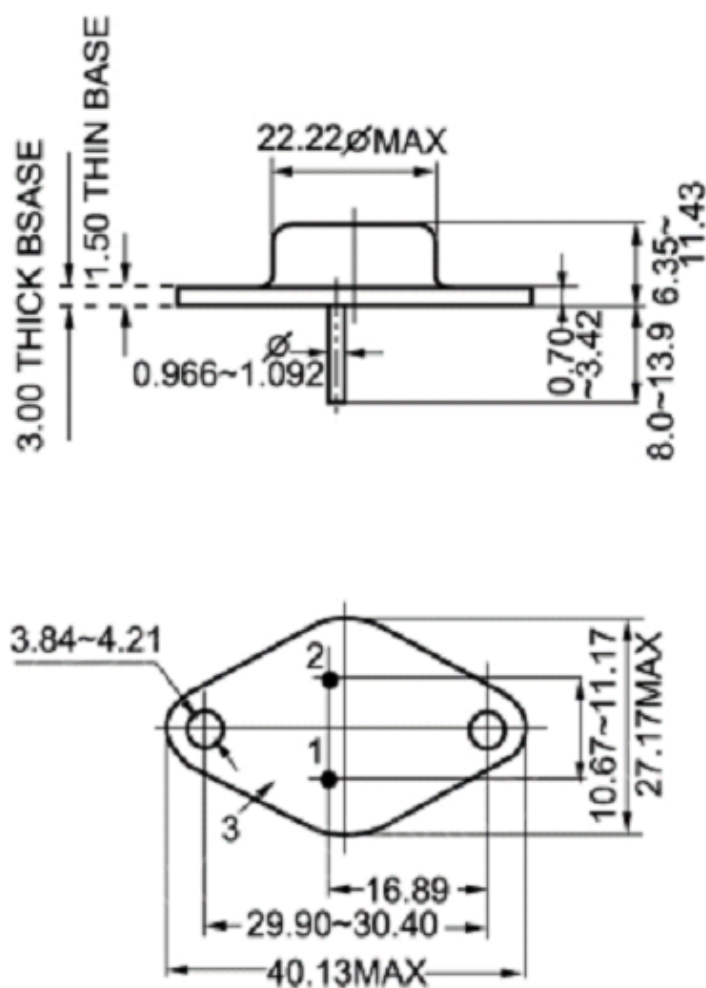


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)